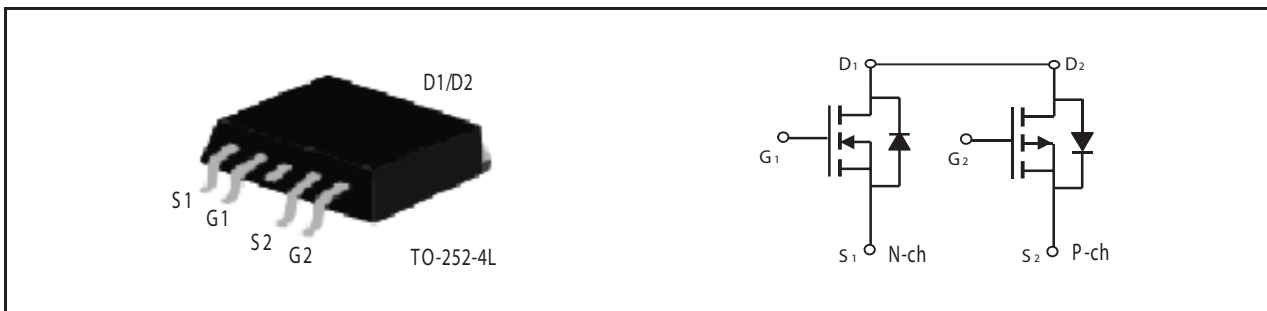




Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRODUCT SUMMARY (N-Channel)		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
40V	14A	27 @ V _{GS} =10V
		41 @ V _{GS} =4.5V

PRODUCT SUMMARY (P-Channel)		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-40V	-12A	37 @ V _{GS} =-10V
		60 @ V _{GS} =-4.5V



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter	N-Channel	P-Channel	Units	
V _{DS}	Drain-Source Voltage	40	-40	V	
V _{GS}	Gate-Source Voltage	±20	±20	V	
I _D	Drain Current-Continuous ^a	T _C =25°C	14	-12	A
		T _C =70°C	11.2	-9.6	A
I _{DM}	-Pulsed ^b	41	-36	A	
E _{AS}	Single Pulse Avalanche Energy ^d	30	49	mJ	
P _D	Maximum Power Dissipation ^a	T _C =25°C	10.5		W
		T _C =70°C	6.7		W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 175		°C	

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case ^a	12	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	60	°C/W

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N-Channel ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =32V , V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.5	1.8	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =14A		22	27	m ohm
		V _{GS} =4.5V , I _D =11.4A		31	41	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =14A		21		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =20V, V _{GS} =0V f=1.0MHz		785		pF
C _{OSS}	Output Capacitance			80		pF
C _{RSS}	Reverse Transfer Capacitance			68		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =20V I _D =1A V _{GS} =10V R _{GEN} =6 ohm		13.2		ns
t _r	Rise Time			13.6		ns
t _{D(OFF)}	Turn-Off Delay Time			16.5		ns
t _f	Fall Time			23		ns
Q _g	Total Gate Charge	V _{DS} =20V, I _D =14A, V _{GS} =10V		15		nC
		V _{DS} =20V, I _D =14A, V _{GS} =4.5V		7.2		nC
Q _{gs}	Gate-Source Charge	V _{DS} =20V, I _D =14A, V _{GS} =10V		1.7		nC
Q _{gd}	Gate-Drain Charge			4.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				2	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V, I _S =2A		0.81	1.2	V

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P-Channel ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-32V, V _{GS} =0V			-1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1.0	-1.8	-3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-12A		30	37	m ohm
		V _{GS} =-4.5V, I _D =-9.4A		45	60	m ohm
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-13A		18		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V f=1.0MHz		863		pF
C _{OSS}	Output Capacitance			142		pF
C _{RSS}	Reverse Transfer Capacitance			92		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =-20V I _D =-1A		14		ns
t _r	Rise Time			15		ns
t _{D(OFF)}	Turn-Off Delay Time	V _{GS} =-10V R _{GEN} =6 ohm		64		ns
t _f	Fall Time			38		ns
Q _g	Total Gate Charge	V _{DS} =-20V, I _D =-12A, V _{GS} =-10V		16.8		nC
		V _{DS} =-20V, I _D =-12A, V _{GS} =-4.5V		8.1		nC
Q _{gs}	Gate-Source Charge	V _{DS} =-20V, I _D =-12A, V _{GS} =-10V		1.8		nC
Q _{gd}	Gate-Drain Charge			4.8		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				-3	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V, I _S =-3A		-0.8	-1.2	V

Notes

- Surface Mounted on FR4 Board, t ≤ 10sec.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 20V, V_{GS}=10V. (See Figure13)

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N-Channel

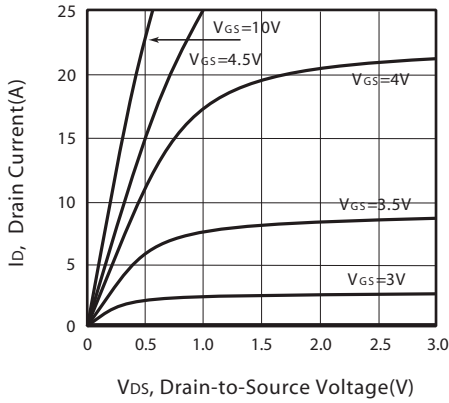


Figure 1. Output Characteristics

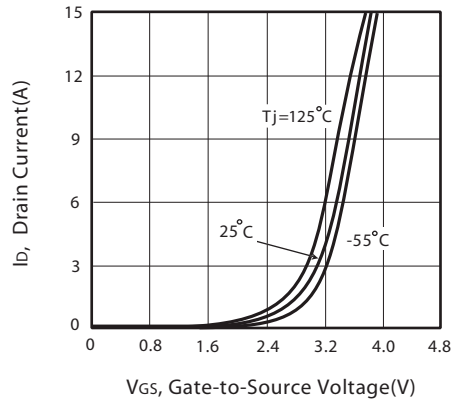


Figure 2. Transfer Characteristics

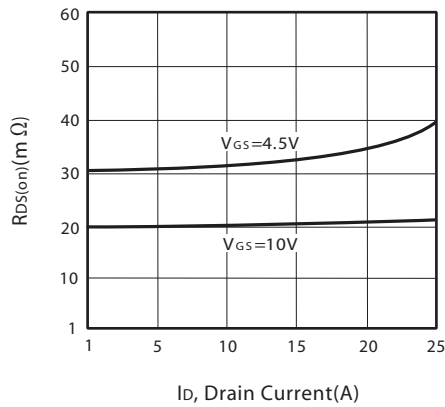


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

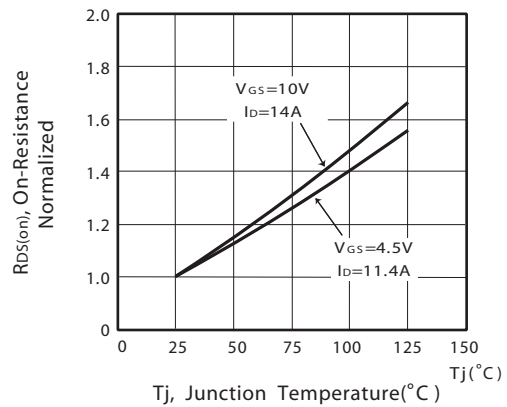


Figure 4. On-Resistance Variation with Drain Current and Temperature

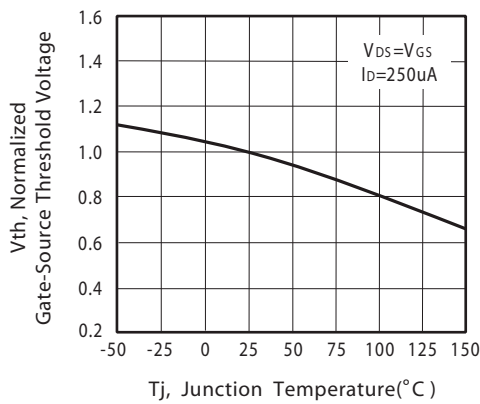


Figure 5. Gate Threshold Variation with Temperature

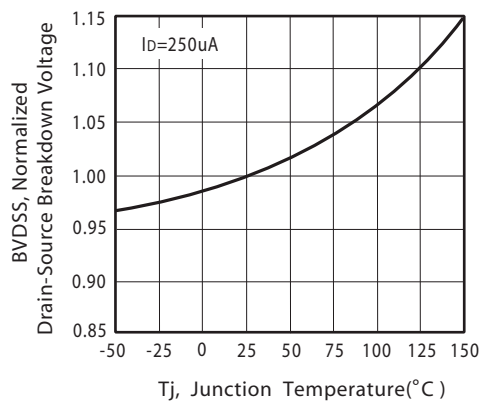


Figure 6. Breakdown Voltage Variation with Temperature

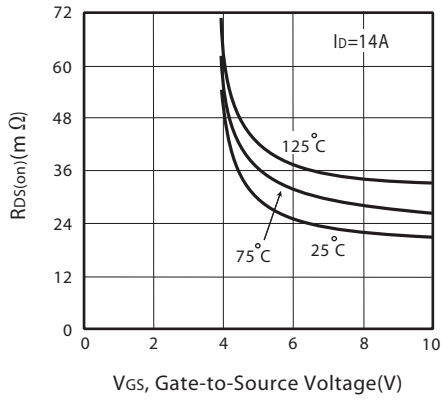


Figure 7. On-Resistance vs. Gate-Source Voltage

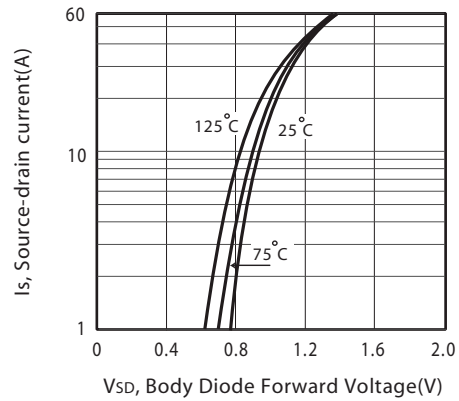


Figure 8. Body Diode Forward Voltage Variation with Source Current

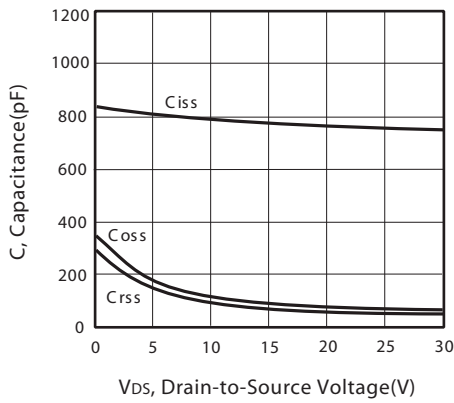


Figure 9. Capacitance

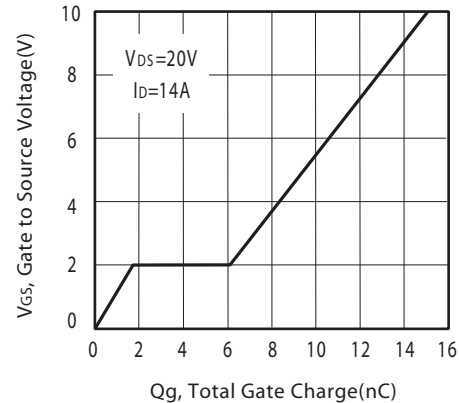


Figure 10. Gate Charge

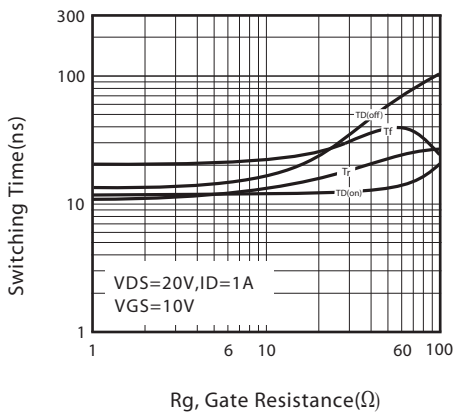


Figure 11. switching characteristics

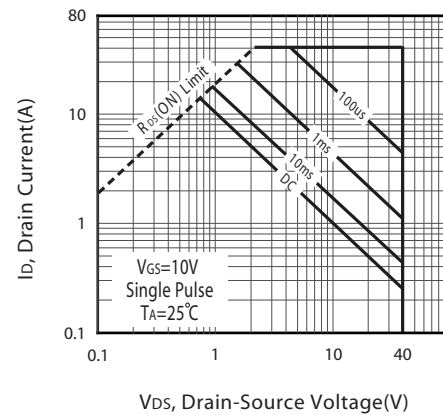
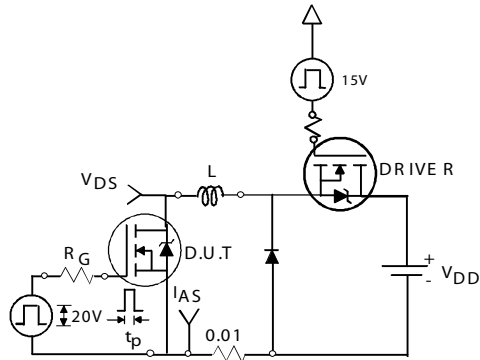
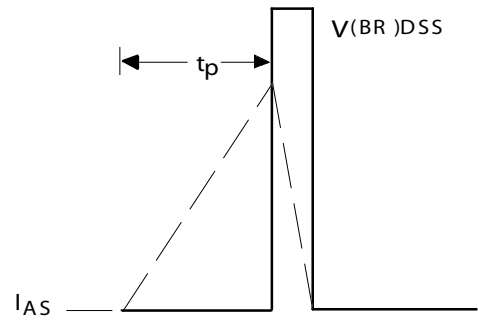


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

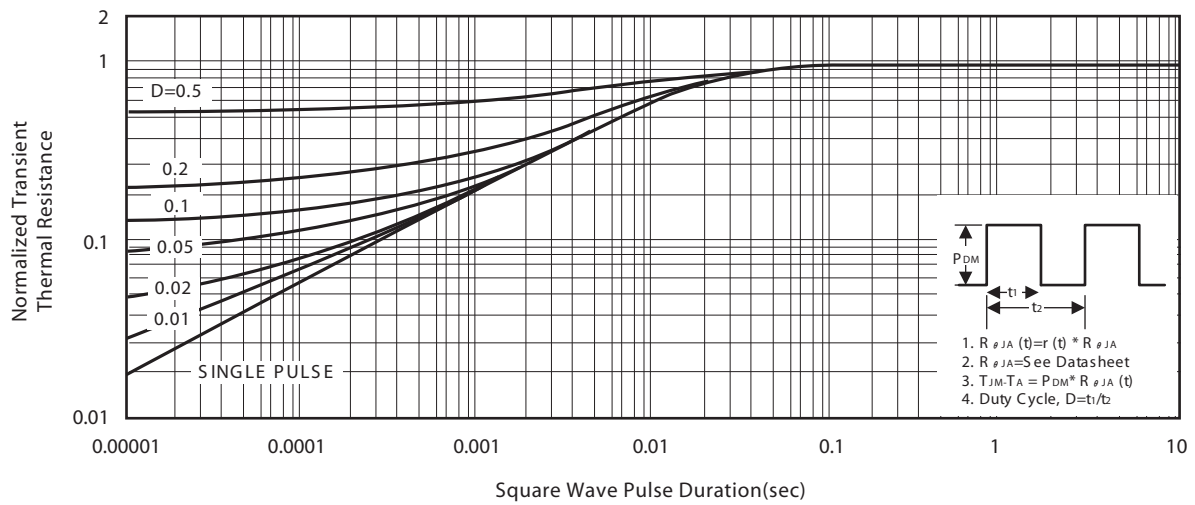


Figure 14. Normalized Thermal Transient Impedance Curve

P-Channel

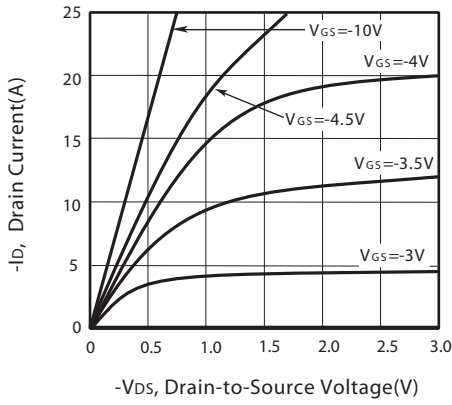


Figure 1. Output Characteristics

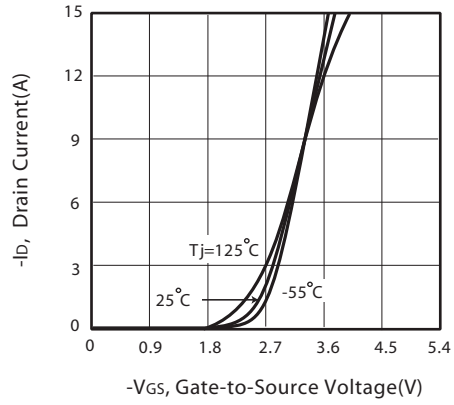


Figure 2. Transfer Characteristics

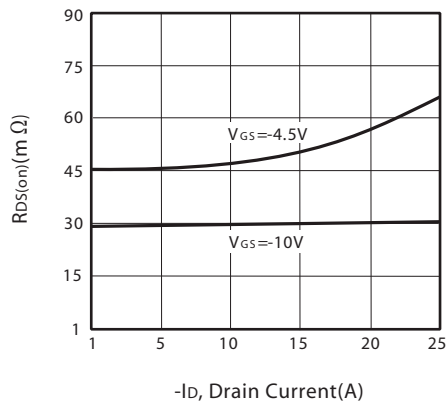


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

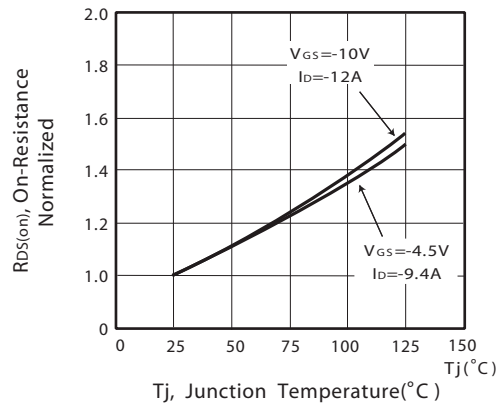


Figure 4. On-Resistance Variation with Drain Current and Temperature

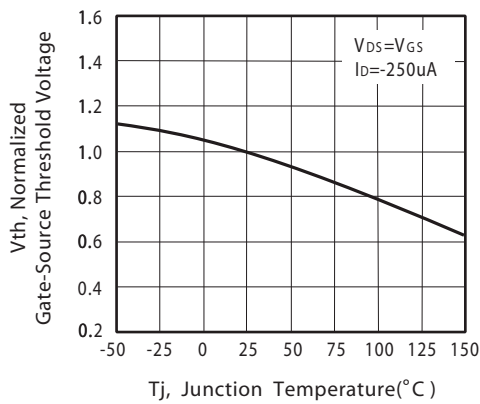


Figure 5. Gate Threshold Variation with Temperature

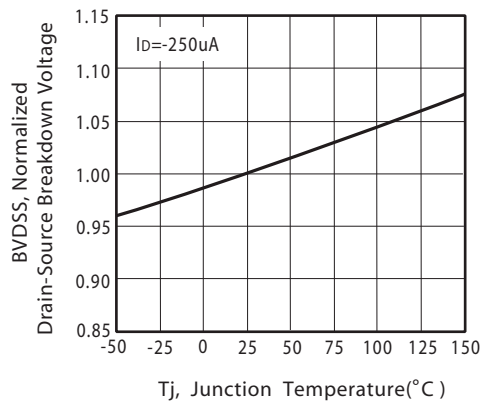


Figure 6. Breakdown Voltage Variation with Temperature

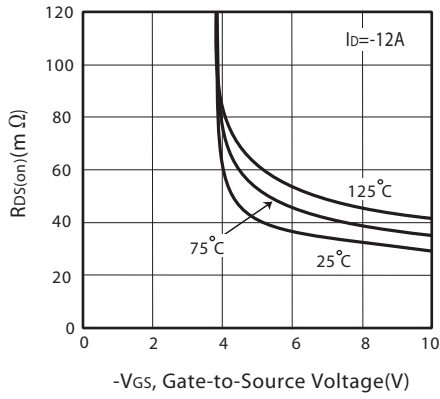


Figure 7. On-Resistance vs. Gate-Source Voltage

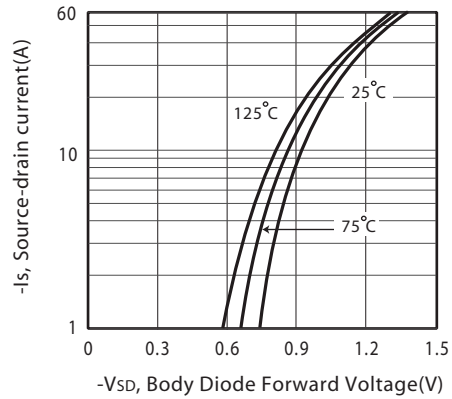


Figure 8. Body Diode Forward Voltage Variation with Source Current

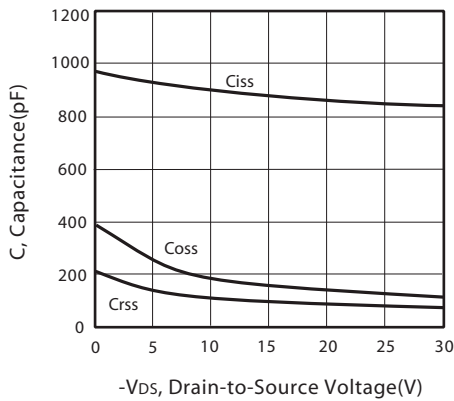


Figure 9. Capacitance

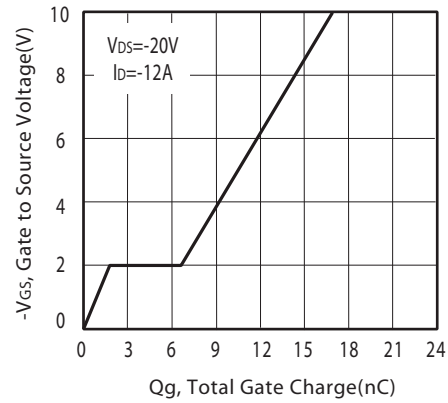


Figure 10. Gate Charge

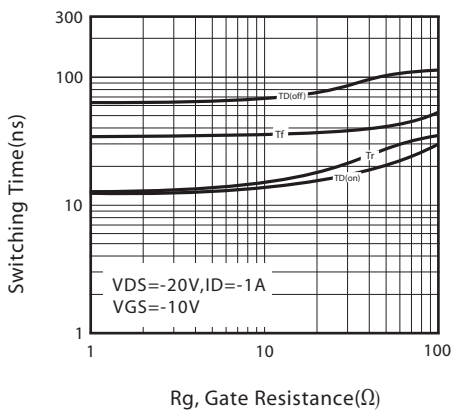


Figure 11. switching characteristics

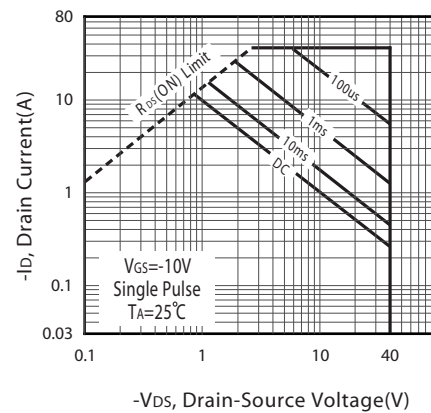
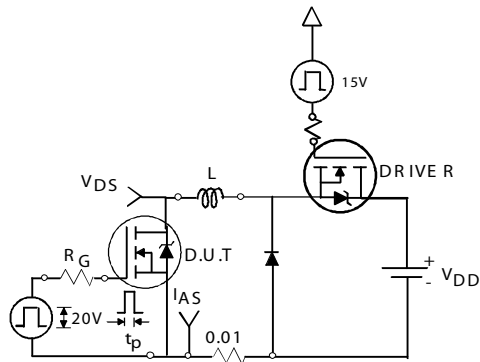
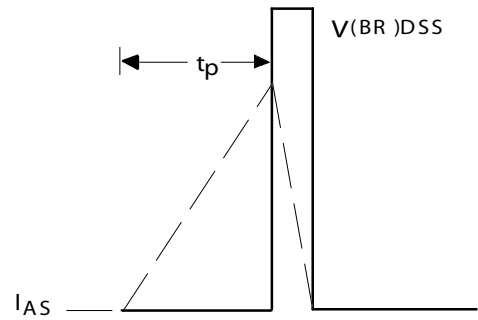


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 15a.



Unclamped Inductive Waveforms

Figure 15b.

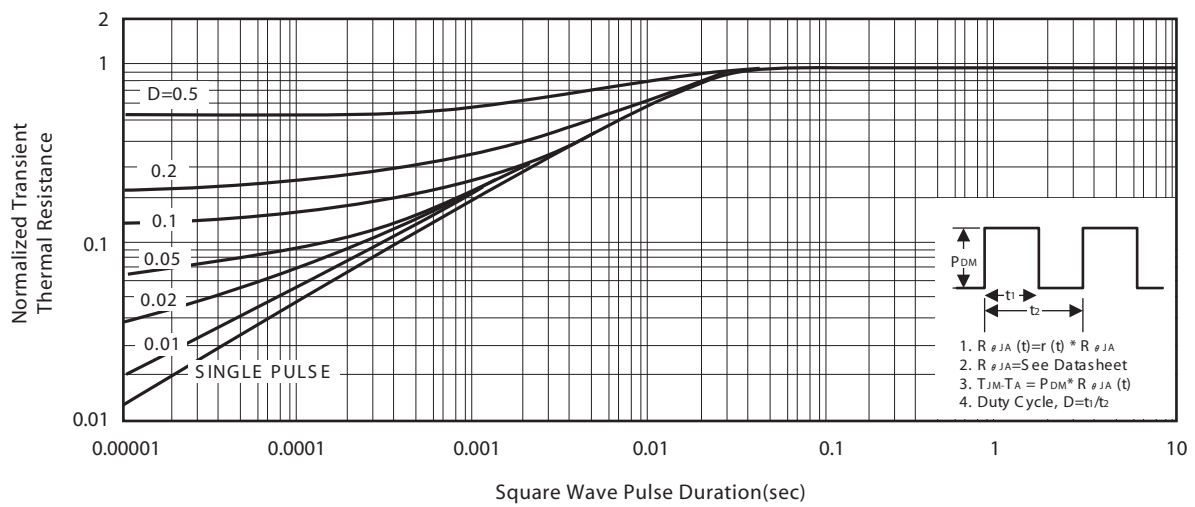
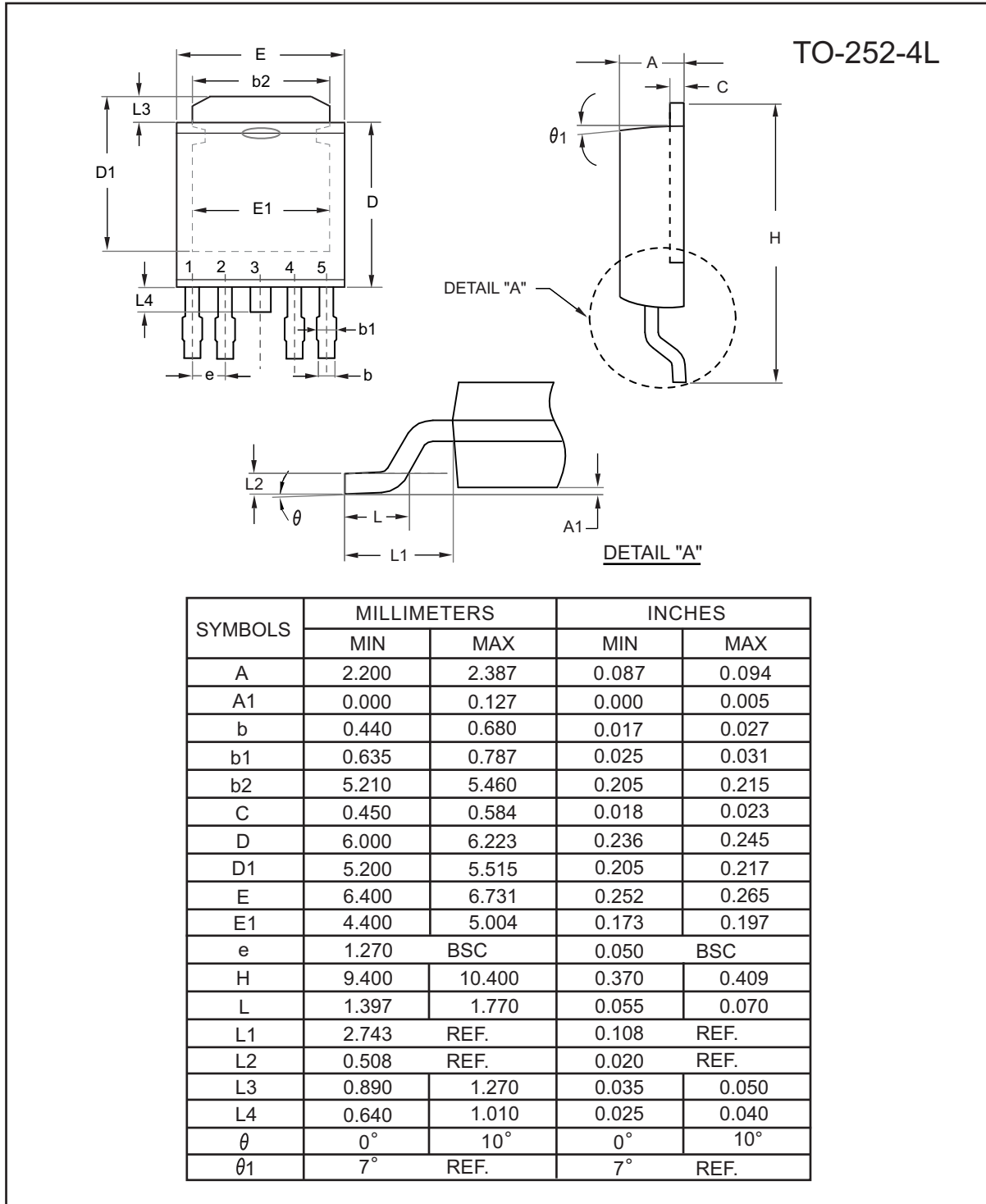


Figure 16. Normalized Thermal Transient Impedance Curve

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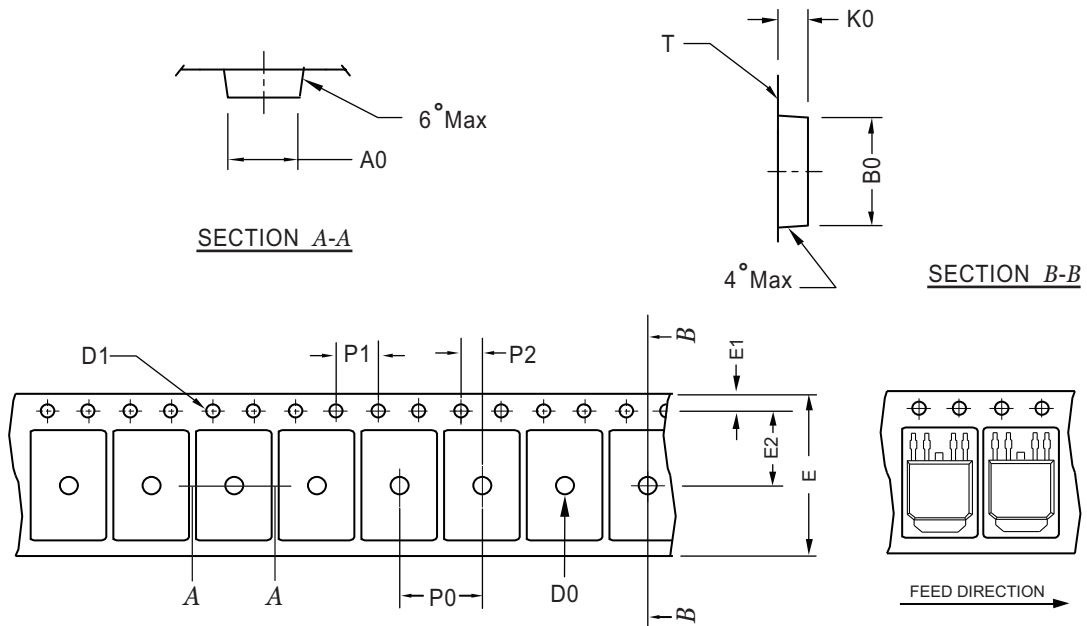
PACKAGE OUTLINE DIMENSIONS



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TO-252-4L Tape and Reel Data

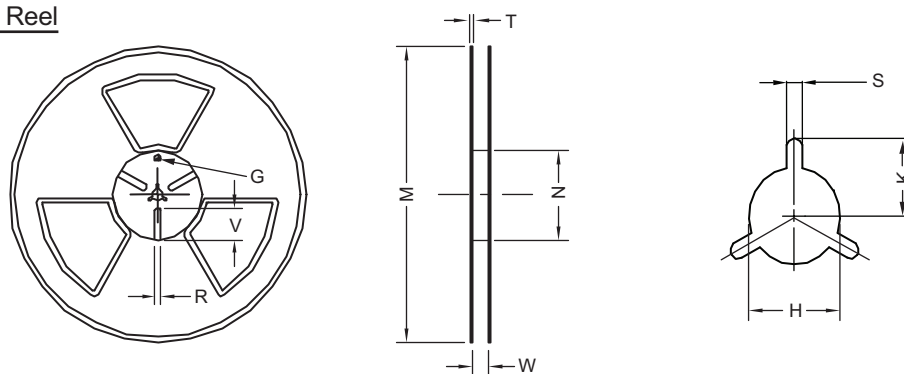
TO-252-4L Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 +0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252-4L Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---